





45V NPN SMALL SIGNAL TRANSISTOR IN DFN1006

Features

- BV_{CEO} > 45V
- I_C = 100mA High Collector Current
- P_D = 1000mW Power Dissipation
- 0.60mm² Package Footprint, 13 times Smaller than SOT23
- 0.5mm Height Package Minimizing Off-Board Profile
- Complementary PNP Type BC857BLP
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

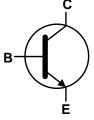
Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu.
- Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0009 grams (Approximate)

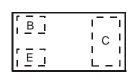








Device Symbol



Top View Device Schematic

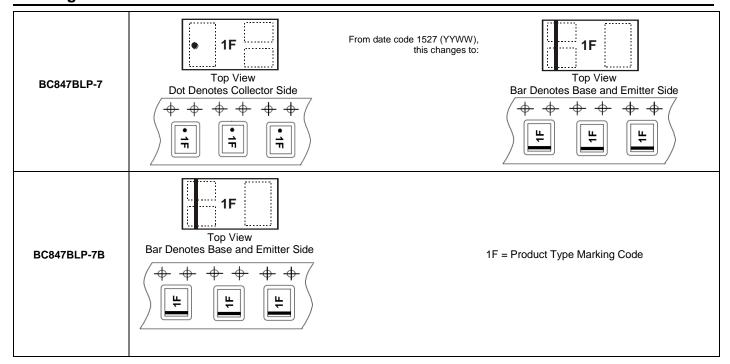
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
BC847BLP-7	1F	7	8mm	3,000
BC847BLP-7B	1F	7	8mm	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	Ic	100	mA
Peak Pulse Collector Current	I _{CM}	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	D-	400	mW	
Power Dissipation	(Note 6)	P _D	1,000		
Thermal Desistance Junction to Ambient	(Note 5)	310		0000	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ hetaJA}$	120	°C/W	
Thermal Resistance, Junction to Lead (Note 7)		$R_{ heta JL}$	120	°C/W	
Operating and Storage and Temperature Rang	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	50	_	_	V	$I_C = 100\mu A, I_B = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	45	_	_	V	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	6	1	-	V	$I_E = 100 \mu A, I_C = 0$
DC Current Gain	h _{FE}	200	350	450		$V_{CE} = 5.0V, I_{C} = 2.0mA$
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(sat)}	1	80 200	250 600	mV	$I_C = 10$ mA, $I_B = 0.5$ mA $I_C = 100$ mA, $I_B = 5.0$ mA
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	1 1	700 900	1 1	mV	$I_C = 10$ mA, $I_B = 0.5$ mA $I_C = 100$ mA, $I_B = 5.0$ mA
Base-Emitter Voltage (Note 9)	V _{BE(ON)}	580 —	640 725	700 770	mV	$V_{CE} = 5.0V, I_{C} = 2.0mA$ $V_{CE} = 5.0V, I_{C} = 10mA$
Collector-Cutoff Current	I _{CBO}	1 1	11	15 5.0	nΑ μΑ	V _{CB} = 30V V _{CB} = 30V, T _A = +150°C
Gain Bandwidth Product	f⊤	100		_	MHz	V _{CE} = 5.0V, I _C = 10mA, f = 100MHz
Collector-Base Capacitance	C _{CBO}	_	3.0	_	pF	V _{CB} = 10V, f = 1.0MHz

Notes:

- 5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.

 6. Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.

 7. Thermal resistance from junction to solder-point (on the exposed collector pad).

 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

 9. Measured under pulsed conditions. Pulse width \$ 300us. Duty cycle \$ 2%.

- 9. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

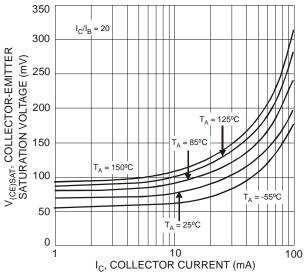


Fig. 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

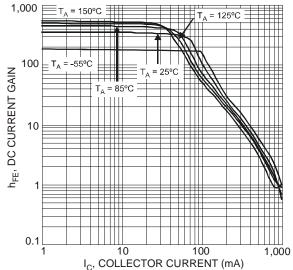


Fig. 5 Typical DC Current Gain vs. Collector Current

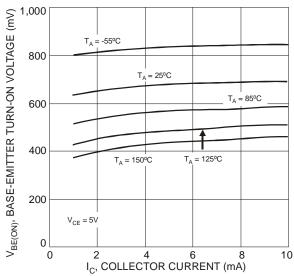


Fig. 3 Typical Base-Emitter Turn-On Voltage vs. Collector Current

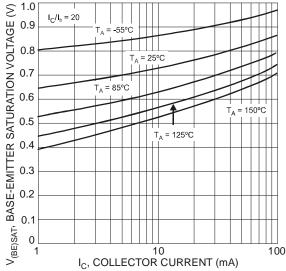
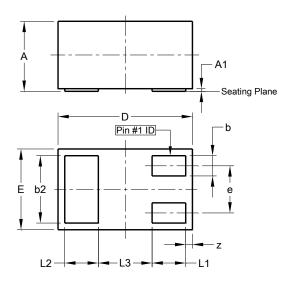


Fig. 4 Typical Base-Emitter Saturation Voltage vs. Collector Current



Package Outline Dimensions

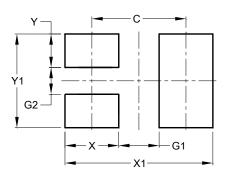
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X1-DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
е	ı	-	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	-	-	0.40		
Z	0.02	0.08	0.05		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70



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